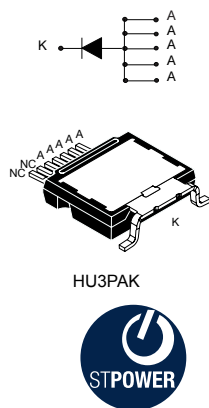


Automotive 650 V, 30 A high surge silicon carbide power Schottky diode



Features

- AEC-Q101 qualified and PPAP capable 
- No reverse recovery charge in application current range
- Switching behavior independent of temperature
- High forward surge capability
- Operating T_j from $-55\text{ }^{\circ}\text{C}$ to $175\text{ }^{\circ}\text{C}$
- SMD with top side cooling package (HU3PAK)
- ECOPACK2 compliant component

Applications

- OBC (On board battery chargers)
- EV Charging station

Description

The SiC diode STPSC30G065L2Y, housed in HU3PAK, is an ultrahigh performance power Schottky rectifier. It is manufactured using a silicon carbide substrate. The wide band-gap material allows the design of a low V_F Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Based on latest technology optimization, this diode has an improved forward surge current capability, making it ideal for use in PFC, where this **ST SiC diode** boosts the performance in hard switching conditions. Using the latest design improvement of the “G” series of ST SiC diodes, as well as implemented tests in production, this diode is becoming the reference point in the combination of efficiency and application robustness to the application design.

Product label



Product status link

[STPSC30G065L2Y](#)

Product summary

$I_{F(AV)}$	30 A
V_{RRM}	650 V
T_j (max.)	$175\text{ }^{\circ}\text{C}$
V_F (typ.)	1.30 V

1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage ($T_j = -55\text{ °C}$ to $+175\text{ °C}$)		650	V
$I_{F(RMS)}$	Forward rms current		63	A
$I_{F(AV)}$	Average forward current	$T_c = 135\text{ °C}$, $\delta = 1$	30	A
I_{FRM}	Repetitive peak forward current	$T_c = 135\text{ °C}$, $T_j = 175\text{ °C}$, $\delta = 0.1$, $f_{sw} > 10\text{ kHz}$	129	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal	$T_c = 25\text{ °C}$	A
			$T_c = 150\text{ °C}$	
		$t_p = 10\text{ }\mu\text{s}$ square	$T_c = 25\text{ °C}$	
T_{stg}	Storage temperature range		-65 to +175	°C
T_j	Operating junction temperature range		-55 to +175	°C

Table 2. Thermal resistance parameters

Symbol	Parameter	Value		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Junction to case	0.50	0.71	°C/W

For more information, please refer to the following application note:

- [TN1378](#) : HU3PAK package mounting and thermal behavior

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	25	300	μA
		$T_j = 175\text{ °C}$		-	150	1200	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 30\text{ A}$	-	1.30	1.45	V
		$T_j = 175\text{ °C}$		-	1.49	1.70	

1. Pulse test: $t_p = 10\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 0.879 \times I_{F(AV)} + 0.027 \times I_F^2 (RMS)$$

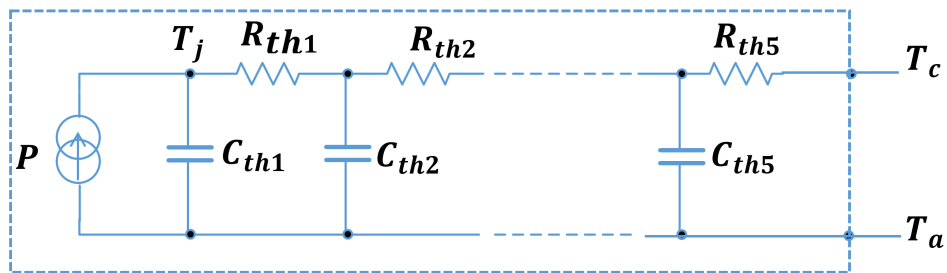
For more information, please refer to the following application notes related to the power losses:

- [AN604](#): Calculation of conduction losses in a power rectifier
- [AN4021](#): Calculation of reverse losses on a power diode

Table 4. Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$Q_{Cj}^{(1)}$	Total capacitive charge	$V_R = 400 \text{ V}$	-	86	-	nC
C_j	Total capacitance	$V_R = 0 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	-	1890	-	pF
		$V_R = 400 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	-	120	-	

1. Most accurate value for the capacitive charge: $Q_{Cj}(V_R) = \int_0^{V_R} C_j(V) dV$

Figure 1. Thermal transient impedance model circuit of the diode – $Z_{th(j-c)}$

Table 5. Components typical values of the diode thermal transient impedance model $Z_{th(j-c)}$

Ref.	Value (K/W)	Ref.	Value (J/K)
R_{th1}	16.73 m	C_{th1}	0.85 m
R_{th2}	116.23 m	C_{th2}	1.34 m
R_{th3}	142.48 m	C_{th3}	2.43 m
R_{th4}	177.96 m	C_{th4}	7.57 m
R_{th5}	45.43 m	C_{th5}	99.02 m

1.1 Characteristics (curves)

Figure 2. Forward voltage drop versus forward current (typical values)

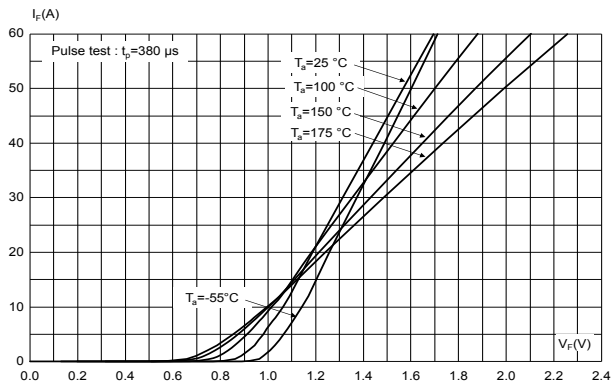


Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

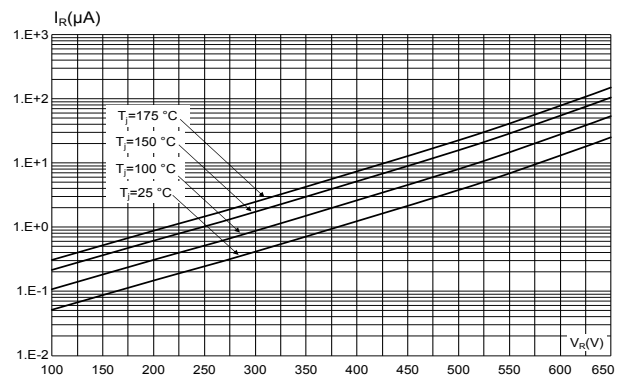


Figure 4. Peak forward current versus case temperature ($f_{sw} > 10$ kHz)

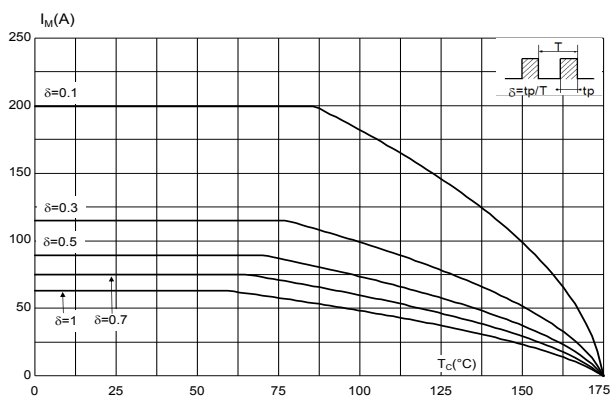


Figure 5. Junction capacitance versus reverse voltage applied (typical values)

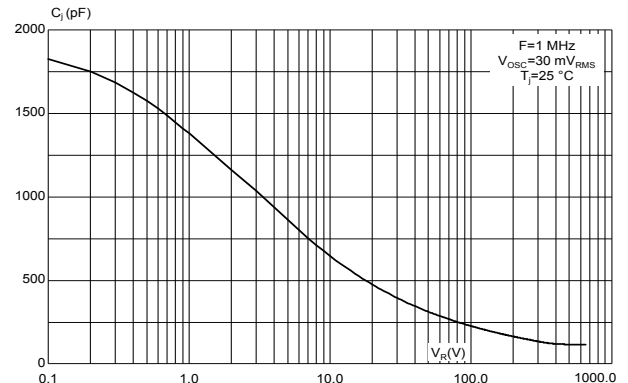


Figure 6. Relative variation of thermal impedance junction to case versus pulse duration

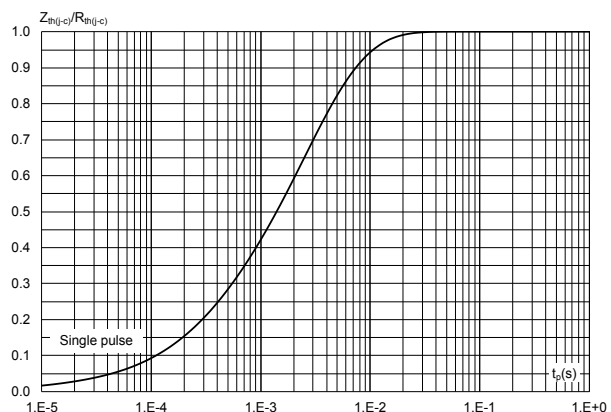


Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

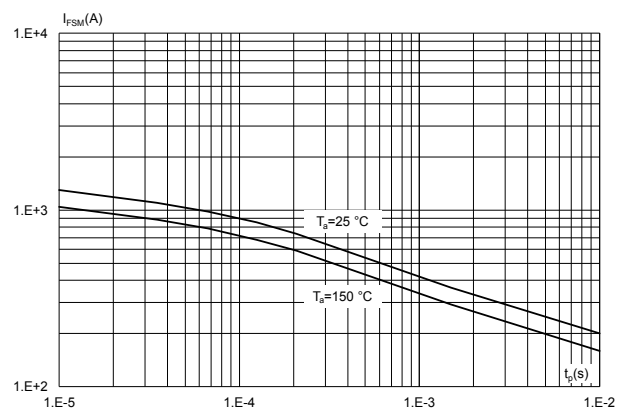
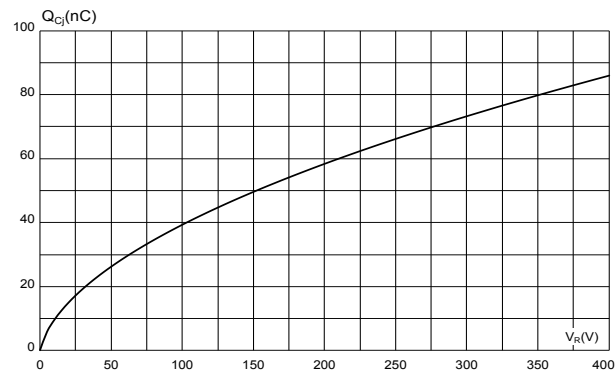


Figure 8. Total capacitive charges versus reverse voltage applied (typical values)



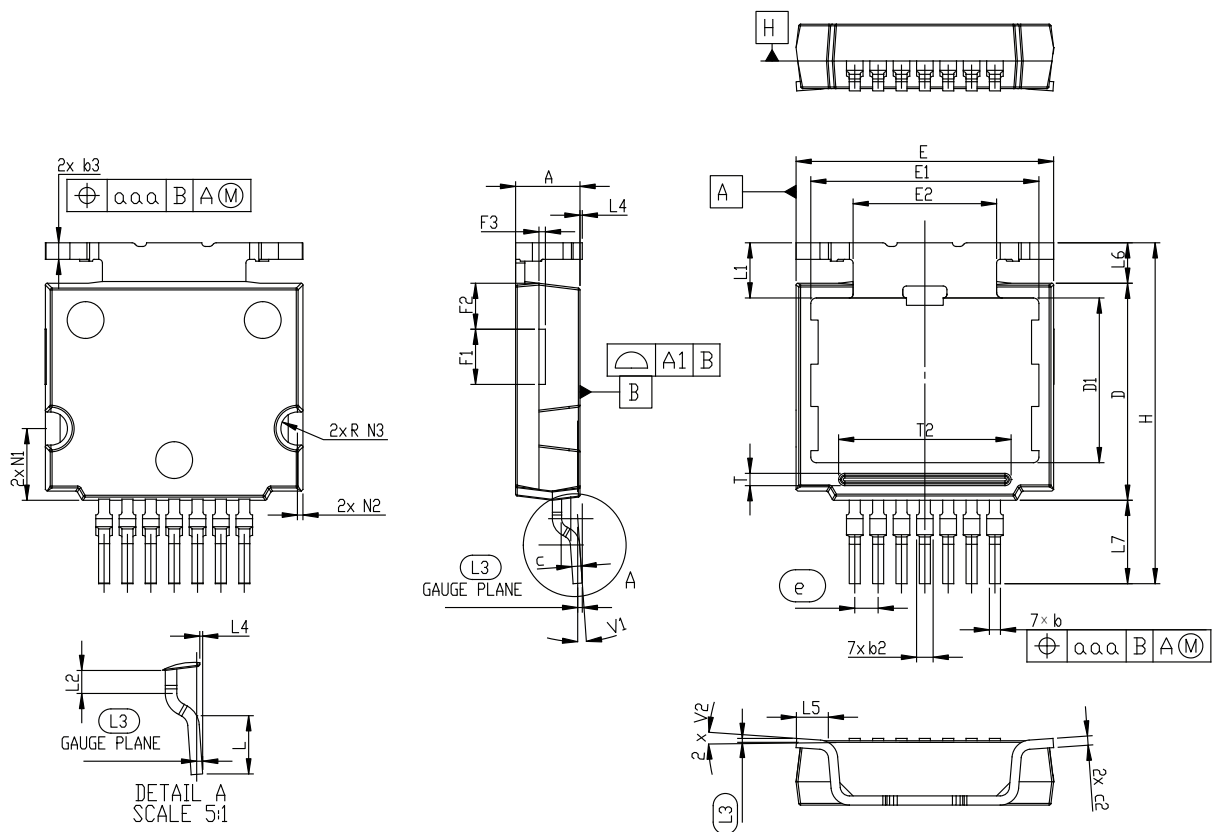
2 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 HU3PAK package information

- Epoxy meets UL94, V0

Figure 9. HU3PAK package outline



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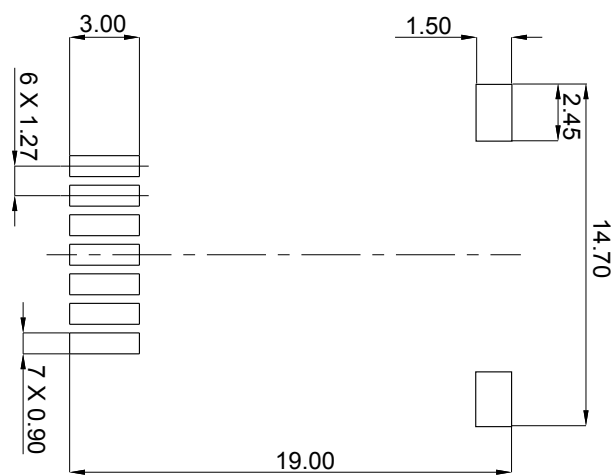
Note: This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 6. HU3PAK package mechanical data

Ref.	Dimensions		
	mm		
	Min.	Typ.	Max.
A	3.40	3.50	3.60
A1		0.05	
b	0.50	0.60	0.70
b2	0.50	0.70	1.00
b3	0.80	0.90	1.00
c	0.40	0.50	0.60
c2	0.40	0.50	0.60
D	11.70	11.80	11.90
D1	8.80	8.955	9.10
E	13.90	14.00	14.10
E1	12.30	12.40	12.50
E2	7.75	7.80	7.85
e	BSC 1.27		
H	18.00	18.58	19.00
L	2.40	2.52	2.60
L1		3.05	
L2	0.90	1.00	1.10
L3	BSC 0.26		
L4	0.075	0.125	0.175
L5	1.83	1.93	2.03
L6	2.14	2.24	2.34
L7	4.44	4.54	4.64
aaa		0.10	
F1	2.90	3.00	3.10
F2	2.40	2.50	2.60
F3	0.25	0.35	0.45
N1	3.80	3.90	4.00
N2	0.25	0.30	0.45
N3	0.80	0.90	1.00
T	0.50	0.67	0.70
T2	9.18	9.38	9.43
θ1		0°	8°
θ2		0°	8°

1. Package outline exclusive of any mold flashes dimensions.
2. Package outline exclusive of burr dimensions.
3. Max resin gate protrusion: 0.25 mm.
4. The planarity of the package backside 50 micron max.
5. BSC: basic spacing between centers

Figure 10. HU3PAK recommended footprint (dimensions are in mm)



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Note: For packing details you can see technical note [TN1173: Packing information for IPAD, protection, rectifiers, thyristors and AC Switches](#).



3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC30G065L2Y	PSC30G065L2Y	HU3PAK	2.34 g	600	Tape and reel

Revision history

Table 8. Document revision history

Date	Revision	Changes
24-Jun-2025	1	Initial release.

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